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## N-channel 650 V, 0.42 $\Omega$ typ., 8 A MDmesh™ M2 Power MOSFET in a TO-220FP package

Datasheet - production data

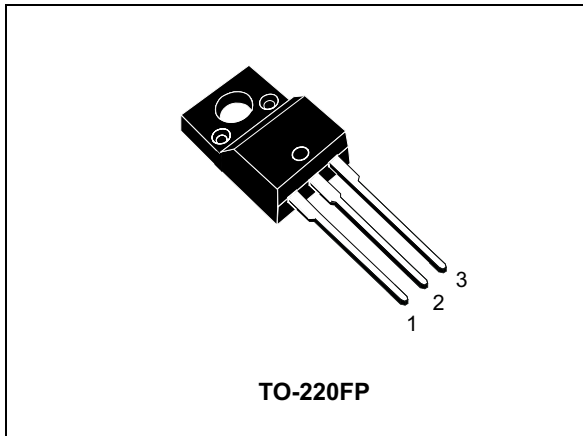
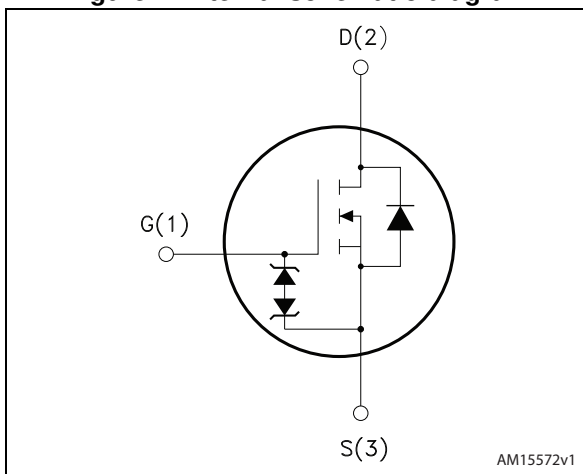


Figure 1. Internal schematic diagram



### Features

Order code	$V_{DS}$	$R_{DS(on) \max}$	$I_D$
STF12N65M2	650 V	0.5 $\Omega$	8 A

- Extremely low gate charge
- Excellent output capacitance ( $C_{oss}$ ) profile
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order code	Marking	Package	Packaging
STF12N65M2	12N65M2	TO-220FP	Tube

## Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	8	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	5	A
$I_{DM}^{(2)}$	Drain current (pulsed)	32	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	25	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(4)}$	MOSFET $dv/dt$ ruggedness	50	V/ns
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t=1\text{ s}; T_C=25\text{ }^\circ\text{C}$ )	2500	V
$T_{stg}$	Storage temperature	- 55 to 150	$^\circ\text{C}$
$T_j$	Max. operating junction temperature		

1. Limited by maximum junction temperature.
2. Pulse width limited by safe operating area.
3.  $I_{SD} \leq 8\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ;  $V_{DS\text{ peak}} < V_{(BR)DSS}$ ,  $V_{DD}=400\text{ V}$ .
4.  $V_{DS} \leq 520\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	5	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$

**Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$ )	1.6	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j=25\text{ }^\circ\text{C}$ , $I_D=I_{AR}$ ; $V_{DD}=50\text{ V}$ )	250	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 5. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 1\text{ mA}$	650			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 650\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0, V_{DS} = 650\text{ V}, T_C = 125\text{ °C}$			100	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 4\text{ A}$		0.42	0.5	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{GS} = 0, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	535	-	pF
$C_{oss}$	Output capacitance		-	25	-	pF
$C_{riss}$	Reverse transfer capacitance		-	1.1	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0\text{ to }520\text{ V}$	-	144	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz open drain}$	-	7	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}, I_D = 8\text{ A}, V_{GS} = 10\text{ V}$ (see <a href="#">Figure 15</a> )	-	16.5	-	nC
$Q_{gs}$	Gate-source charge		-	2.6	-	nC
$Q_{gd}$	Gate-drain charge		-	8.5	-	nC

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325 \text{ V}$ , $I_D = 4 \text{ A}$ , $R_G = 4.7 \text{ } \Omega$ , $V_{GS} = 10 \text{ V}$ (see <a href="#">Figure 14</a> and <a href="#">19</a> )	-	9	-	ns
$t_r$	Rise time		-	7	-	ns
$t_{d(off)}$	Turn-off delay time		-	34	-	ns
$t_f$	Fall time		-	13.5	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		8	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		32	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0$ , $I_{SD} = 8 \text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 8 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 16</a> )	-	313		ns
$Q_{rr}$	Reverse recovery charge		-	2.7		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	17		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 8 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ , $T_j = 150 \text{ } ^\circ\text{C}$ (see <a href="#">Figure 16</a> )	-	462		ns
$Q_{rr}$	Reverse recovery charge		-	4.1		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	17.5		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

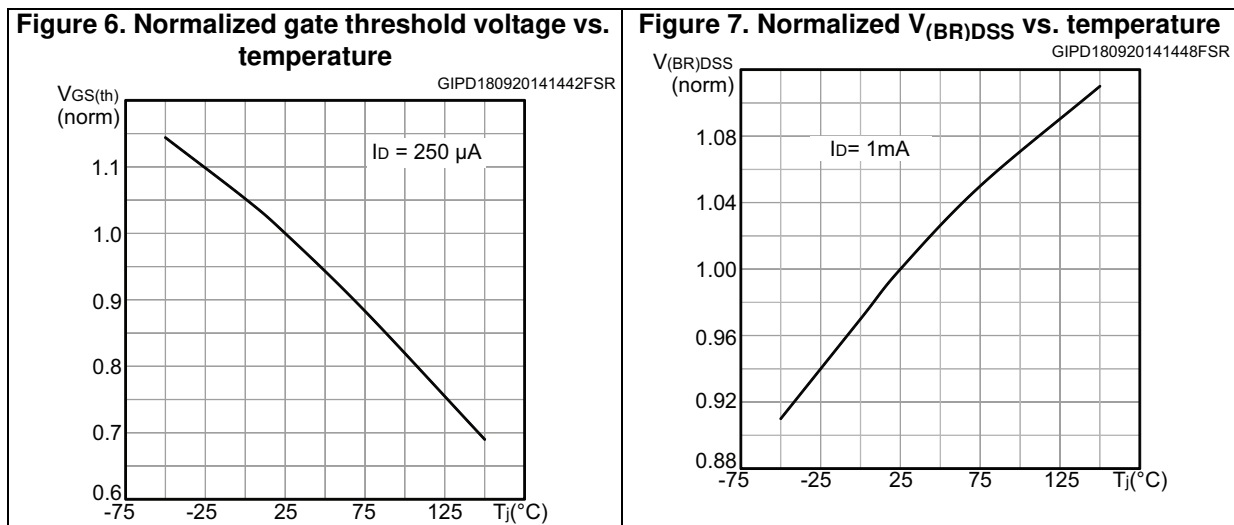
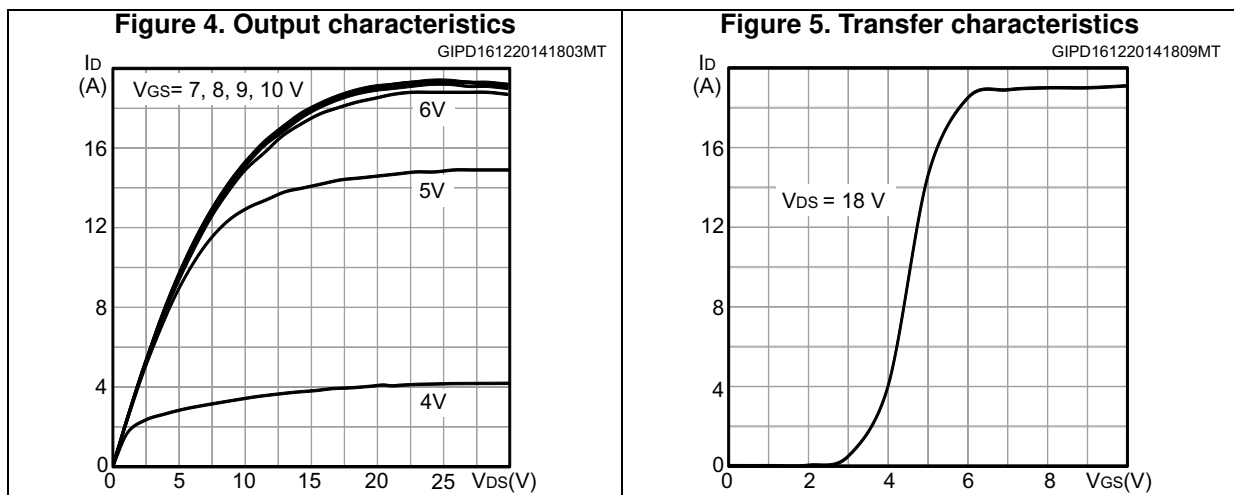
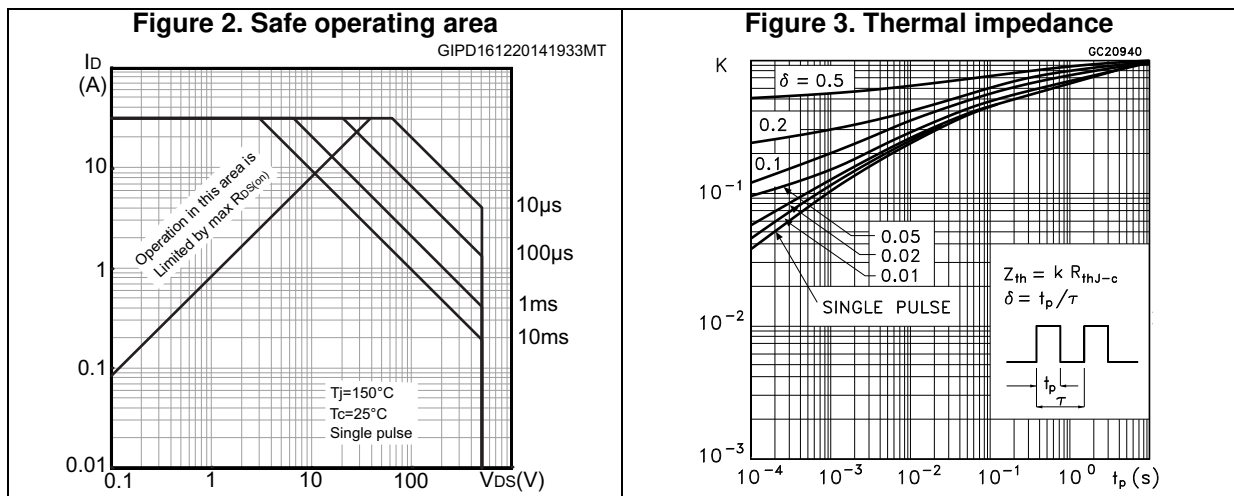


Figure 8. Static drain-source on-resistance

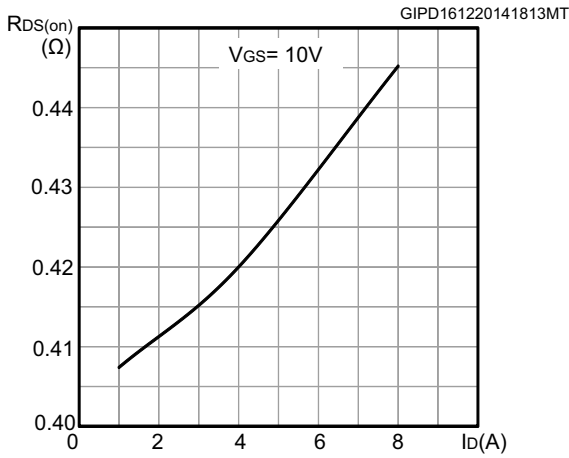


Figure 9. Normalized on-resistance vs. temperature

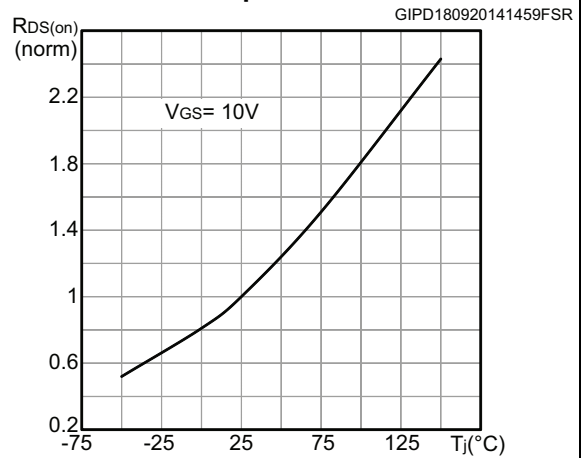


Figure 10. Gate charge vs. gate-source voltage

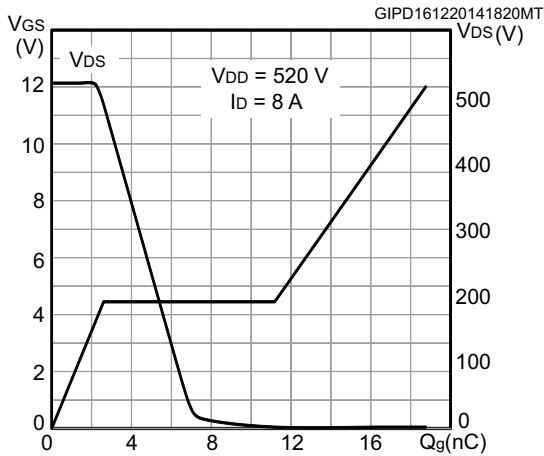


Figure 11. Capacitance variations

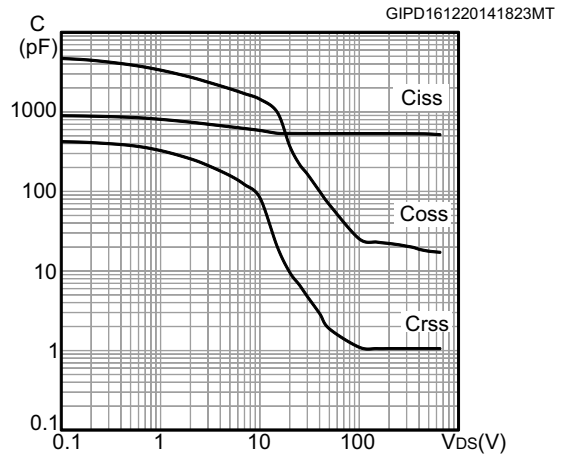


Figure 12. Output capacitance stored energy

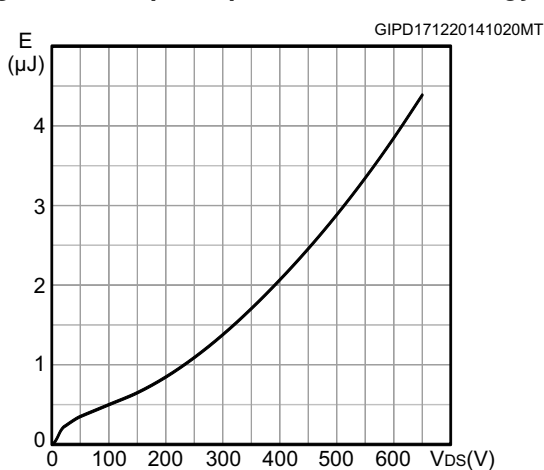
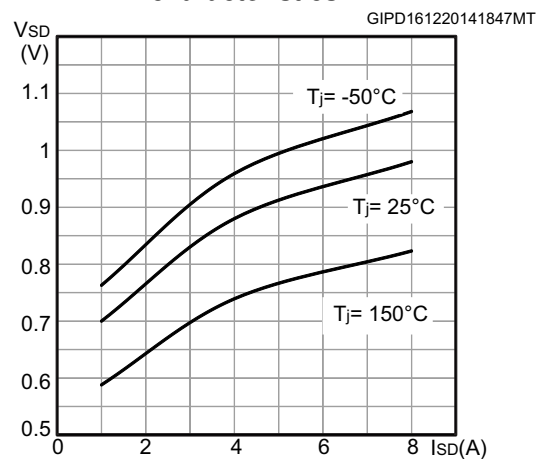
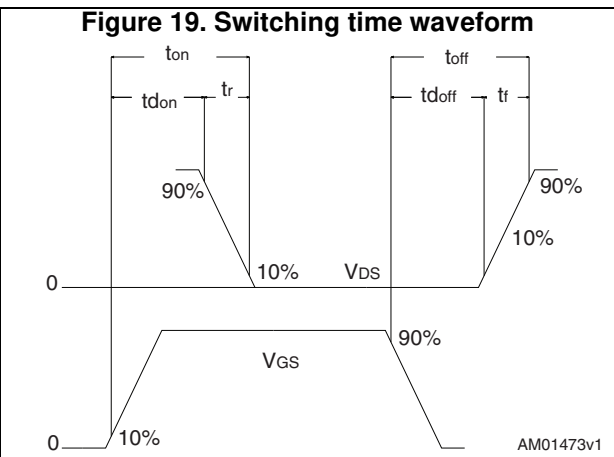
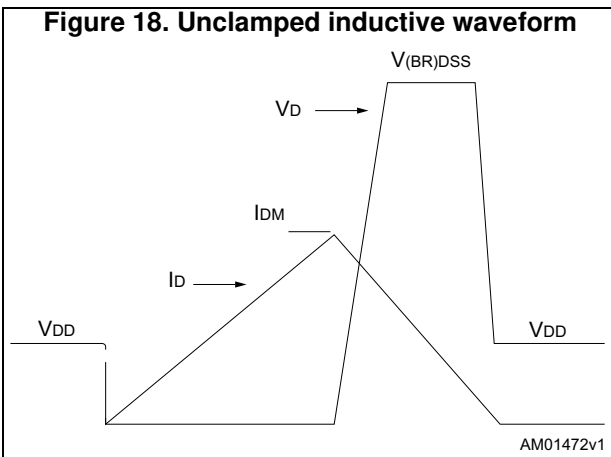
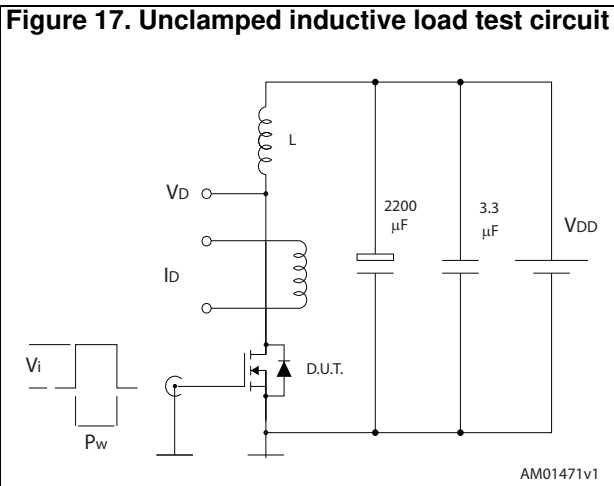
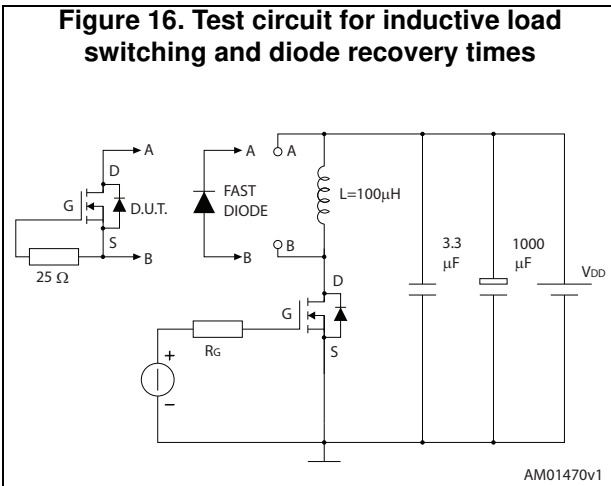
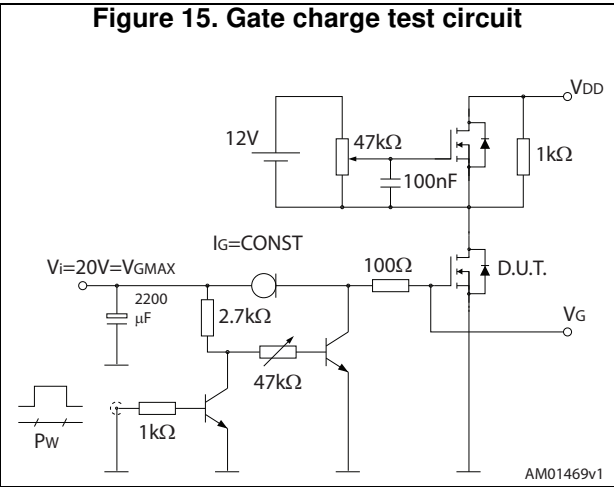
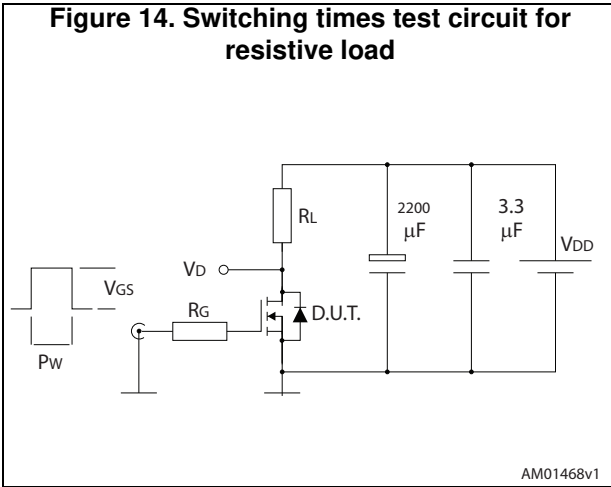


Figure 13. Source-drain diode forward characteristics



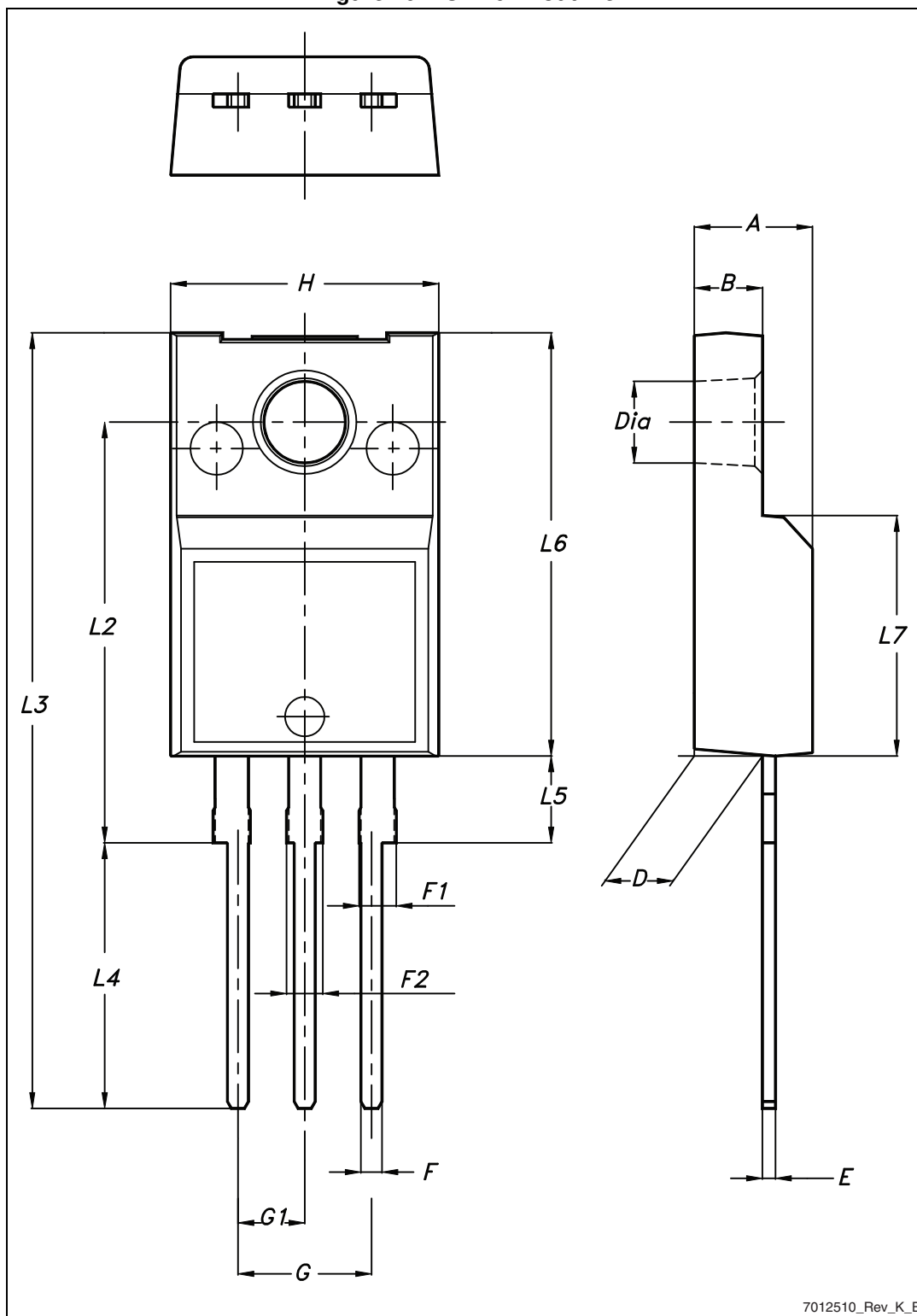
### 3 Test circuits



## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Figure 20. TO-220FP outline



7012510\_Rev\_K\_B

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Ø	3		3.2

## 5 Revision history

**Table 10. Document revision history**

<b>Date</b>	<b>Revision</b>	<b>Changes</b>
16-Dec-2014	1	First release.
11-Mar-2015	2	Updated features in cover page. Minor text changes.

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